

General Description

- Trench Power AlphaMOS-II technology
- Low $R_{DS(ON)}$
- Low C_{iss} and C_{rss}
- High Current Capability

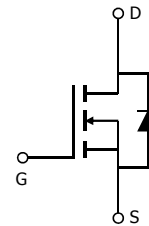
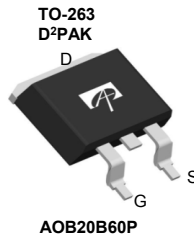
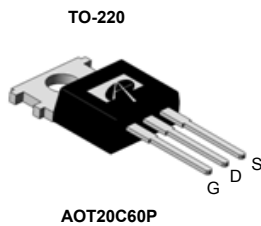
Applications

- General Lighting for LED and CCFL
- AC/DC Power supplies for Industrial, Consumer, and Telecom

Product Summary

$V_{DS} @ T_{j,max}$	700V
I_{DM}	80A
$R_{DS(ON),max}$	< 0.26 Ω
$Q_{g,typ}$	52nC
$E_{oss} @ 400V$	8.2 μ J

100% UIS Tested
 100% R_g Tested



Orderable Part Number	Package Type	Form	Minimum Order Quantity
AOT20C60PL	TO-220 Green	Tube	1000
AOB20C60PL	TO-263 Green	Tape & Reel	800

Absolute Maximum Ratings $T_A=25^\circ\text{C}$ unless otherwise noted

Parameter	Symbol	Maximum	Units
Drain-Source Voltage	V_{DS}	600	V
Gate-Source Voltage	V_{GS}	± 30	V
Continuous Drain Current	I_D	$T_C=25^\circ\text{C}$	20
		$T_C=100^\circ\text{C}$	16
Pulsed Drain Current ^C	I_{DM}	80	A
Avalanche Current ^C $L=1\text{mH}$	I_{AR}	20	A
Repetitive avalanche energy ^C	E_{AR}	200	mJ
Single pulsed avalanche energy ^G	E_{AS}	1599	mJ
MOSFET dv/dt ruggedness		100	V/ns
Peak diode recovery dv/dt	dv/dt	20	V/ns
Power Dissipation ^B	P_D	$T_C=25^\circ\text{C}$	463
		Derate above 25°C	3.7
Junction and Storage Temperature Range	T_J, T_{STG}	-55 to 150	$^\circ\text{C}$
Maximum lead temperature for soldering purpose, 1/8" from case for 5 seconds	T_L	300	$^\circ\text{C}$

Thermal Characteristics

Parameter	Symbol	Maximum	Units
Maximum Junction-to-Ambient ^{A,D}	$R_{\theta JA}$	65	$^\circ\text{C}/\text{W}$
Maximum Case-to-sink ^A	$R_{\theta CS}$	0.5	$^\circ\text{C}/\text{W}$
Maximum Junction-to-Case	$R_{\theta JC}$	0.27	$^\circ\text{C}/\text{W}$

Electrical Characteristics (T_J=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units	
STATIC PARAMETERS							
BV _{DSS}	Drain-Source Breakdown Voltage	I _D =250μA, V _{GS} =0V, T _J =25°C	600			V	
		I _D =250μA, V _{GS} =0V, T _J =150°C		700			
BV _{DSS} /ΔT _J	Breakdown Voltage Temperature Coefficient	I _D =250μA, V _{GS} =0V		0.54		V/°C	
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =600V, V _{GS} =0V			1	μA	
		V _{DS} =480V, T _J =125°C			10		
I _{GSS}	Gate-Body leakage current	V _{DS} =0V, V _{GS} =±30V			±100	nA	
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =5V, I _D =250μA	3	3.8	5	V	
R _{DS(ON)}	Static Drain-Source On-Resistance	V _{GS} =10V, I _D =10A		0.225	0.26	Ω	
g _{FS}	Forward Transconductance	V _{DS} =40V, I _D =10A		20		S	
V _{SD}	Diode Forward Voltage	I _S =1A, V _{GS} =0V		0.7	1	V	
I _S	Maximum Body-Diode Continuous Current				20	A	
I _{SM}	Maximum Body-Diode Pulsed Current ^C				80	A	
DYNAMIC PARAMETERS							
C _{ISS}	Input Capacitance	V _{GS} =0V, V _{DS} =100V, f=1MHz		3607		pF	
C _{OSS}	Output Capacitance				140		pF
C _{o(er)}	Effective output capacitance, energy related ^H	V _{GS} =0V, V _{DS} =0 to 480V, f=1MHz		95		pF	
C _{o(tr)}	Effective output capacitance, time related ^I				182		pF
C _{RSS}	Reverse Transfer Capacitance	V _{GS} =0V, V _{DS} =100V, f=1MHz		3.3		pF	
R _g	Gate resistance	f=1MHz		2		Ω	
SWITCHING PARAMETERS							
Q _g	Total Gate Charge	V _{GS} =10V, V _{DS} =480V, I _D =20A		52	80	nC	
Q _{gs}	Gate Source Charge			20			nC
Q _{gd}	Gate Drain Charge			14			nC
t _{D(on)}	Turn-On Delay Time	V _{GS} =10V, V _{DS} =300V, I _D =20A, R _G =25Ω		77		ns	
t _r	Turn-On Rise Time			67			ns
t _{D(off)}	Turn-Off Delay Time			120			ns
t _f	Turn-Off Fall Time			43			ns
t _{rr}	Body Diode Reverse Recovery Time	I _F =20A, dI/dt=100A/μs, V _{DS} =100V		599		ns	
Q _{rr}	Body Diode Reverse Recovery Charge	I _F =20A, dI/dt=100A/μs, V _{DS} =100V		11		μC	

A. The value of R_{θJA} is measured with the device in a still air environment with T_A=25°C.

B. The power dissipation P_D is based on T_{J(MAX)}=150°C, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heatsinking is used.

C. Repetitive rating, pulse width limited by junction temperature T_{J(MAX)}=150°C. Ratings are based on low frequency and duty cycles to keep initial T_J=25°C.

D. The R_{θJA} is the sum of the thermal impedance from junction to case R_{θJC} and case to ambient.

E. The static characteristics in Figures 1 to 6 are obtained using <300μs pulses, duty cycle 0.5% max.

F. These curves are based on the junction-to-case thermal impedance which is measured with the device mounted to a large heatsink, assuming a maximum junction temperature of T_{J(MAX)}=150°C. The SOA curve provides a single pulse rating.

G. L=60mH, I_{AS}=7.3A, V_{DD}=150V, R_G=25Ω, Starting T_J=25°C.

H. C_{o(er)} is a fixed capacitance that gives the same stored energy as C_{OSS} while V_{DS} is rising from 0 to 80% V_{(BR)DSS}.

I. C_{o(tr)} is a fixed capacitance that gives the same charging time as C_{OSS} while V_{DS} is rising from 0 to 80% V_{(BR)DSS}.

THIS PRODUCT HAS BEEN DESIGNED AND QUALIFIED FOR THE CONSUMER MARKET. APPLICATIONS OR USES AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS ARE NOT AUTHORIZED. AOS DOES NOT ASSUME ANY LIABILITY ARISING OUT OF SUCH APPLICATIONS OR USES OF ITS PRODUCTS. AOS RESERVES THE RIGHT TO IMPROVE PRODUCT DESIGN, FUNCTIONS AND RELIABILITY WITHOUT NOTICE.

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

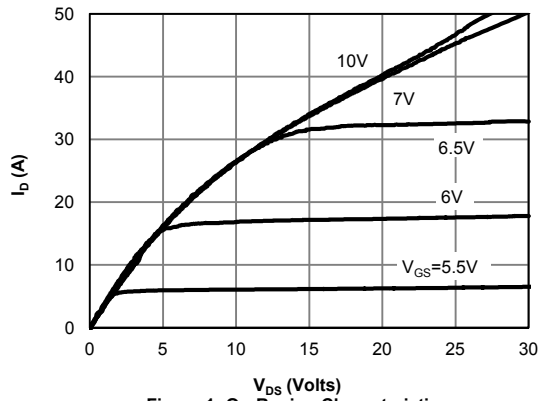


Figure 1: On-Region Characteristics

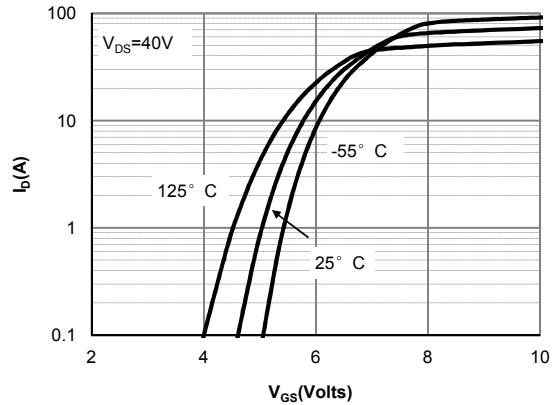


Figure 2: Transfer Characteristics

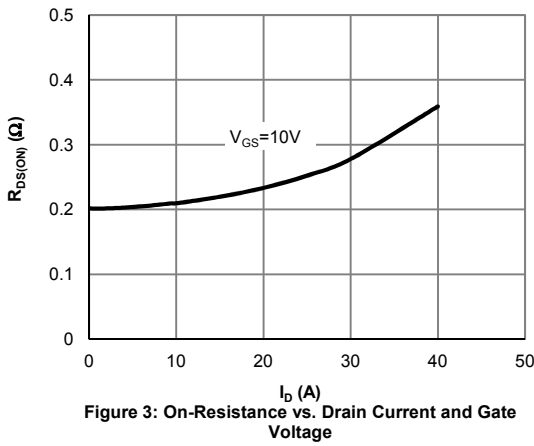


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

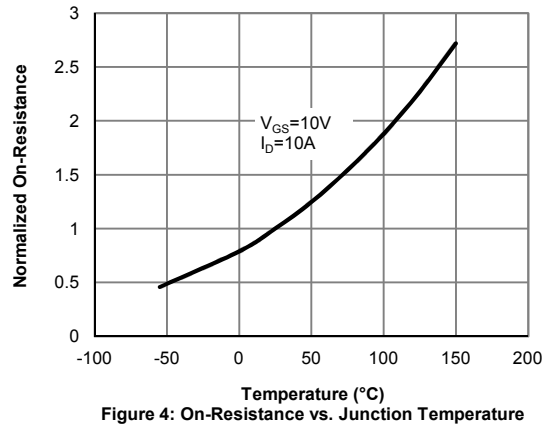


Figure 4: On-Resistance vs. Junction Temperature

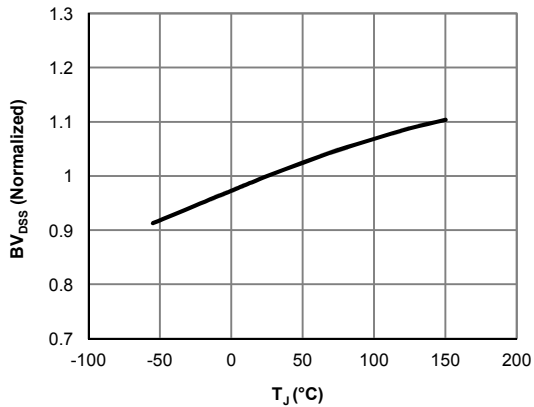


Figure 5: Break Down vs. Junction Temperature

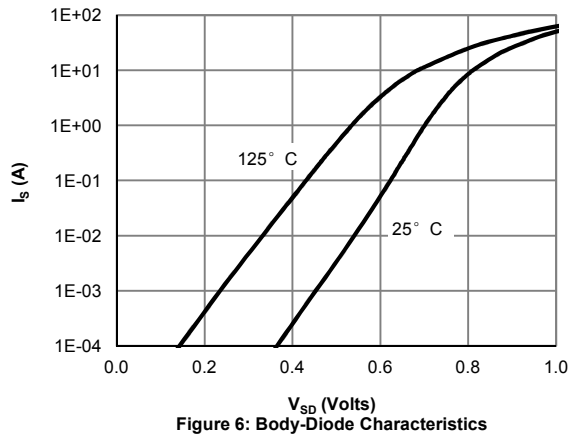


Figure 6: Body-Diode Characteristics

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

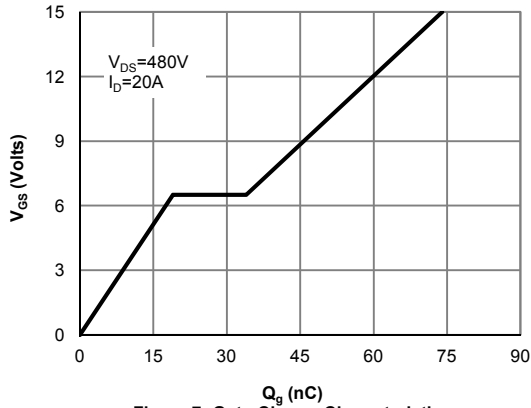


Figure 7: Gate-Charge Characteristics

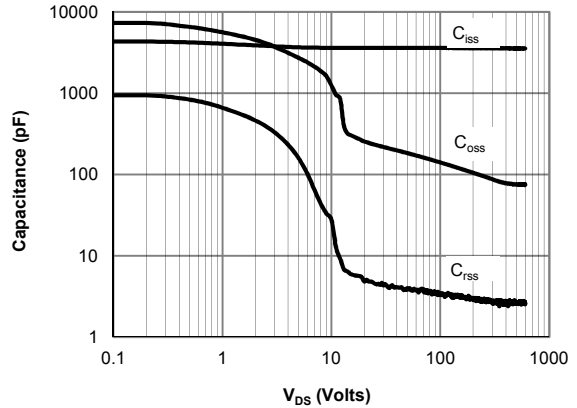


Figure 8: Capacitance Characteristics

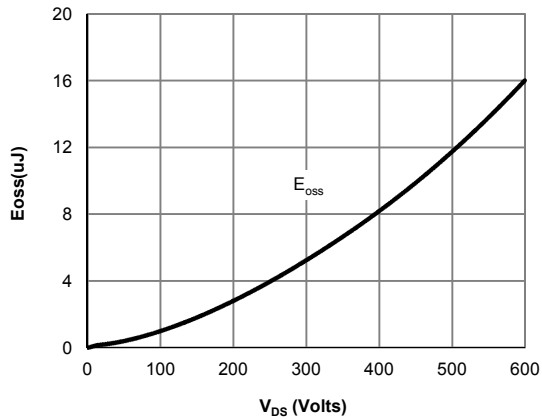


Figure 9: Coss stored Energy

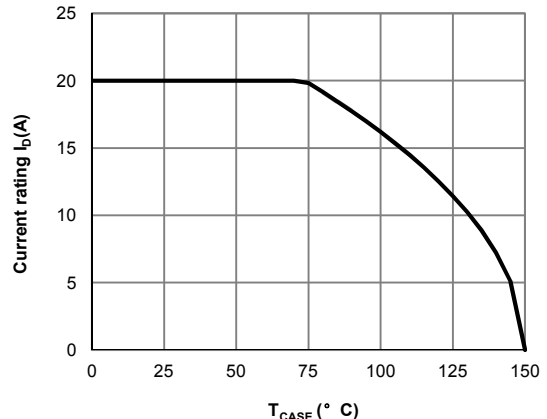


Figure 10: Current De-rating (Note F)

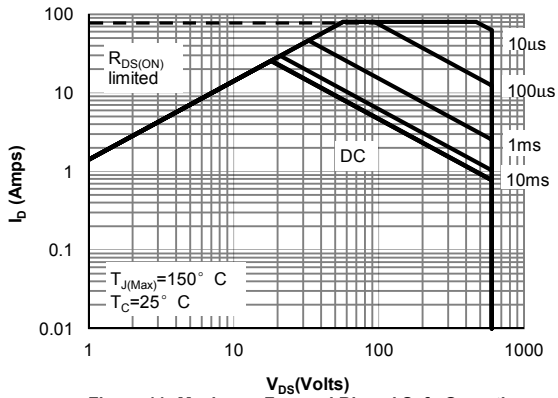


Figure 11: Maximum Forward Biased Safe Operating Area for TO-220/TO-263 Green (Note F)

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

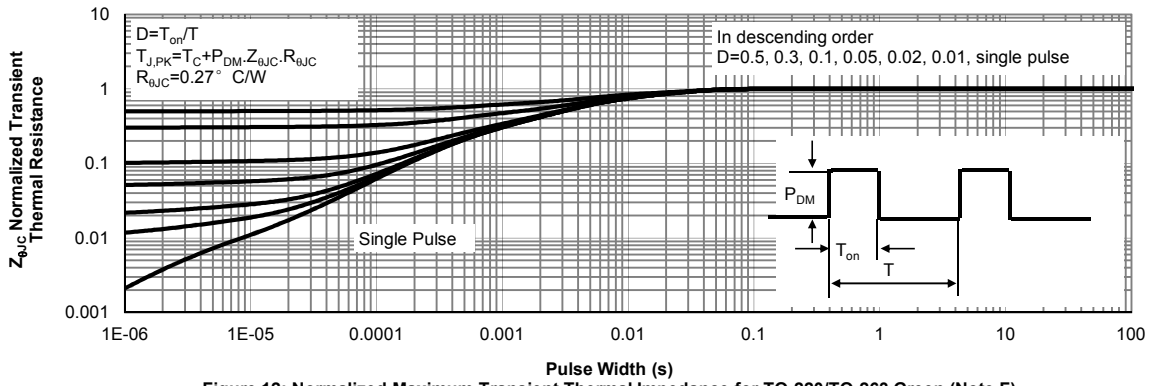
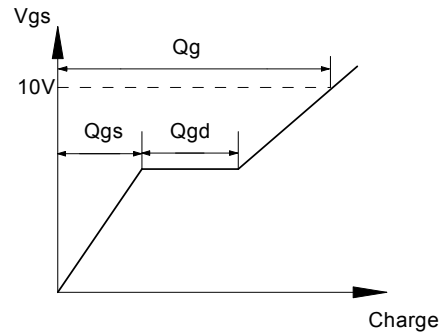
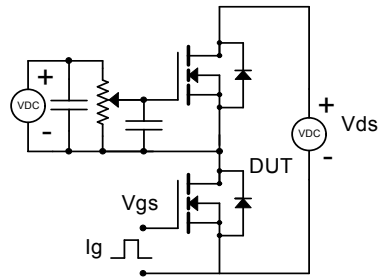
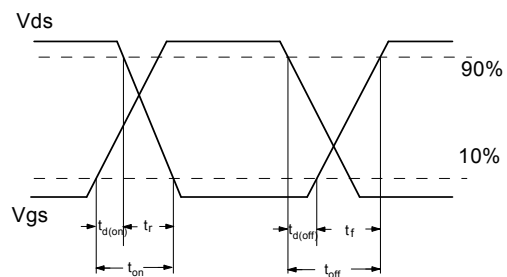
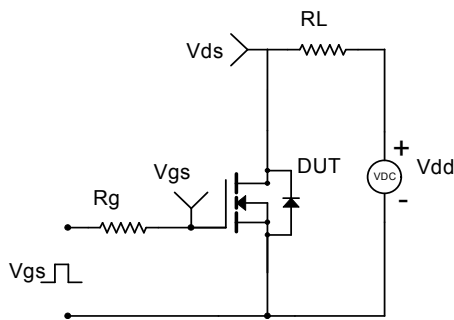


Figure 12: Normalized Maximum Transient Thermal Impedance for TO-220/TO-263 Green (Note F)

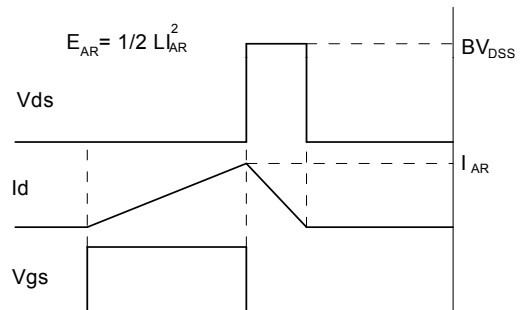
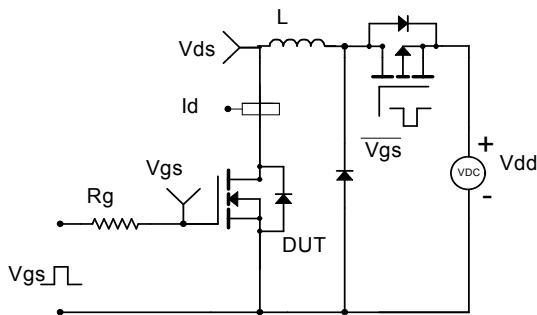
Gate Charge Test Circuit & Waveform



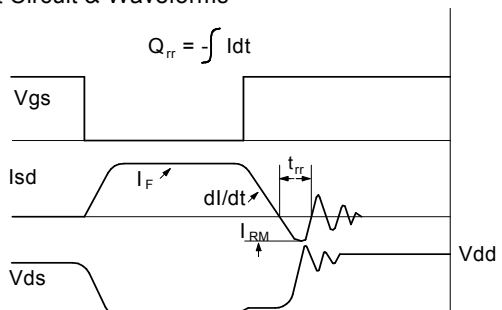
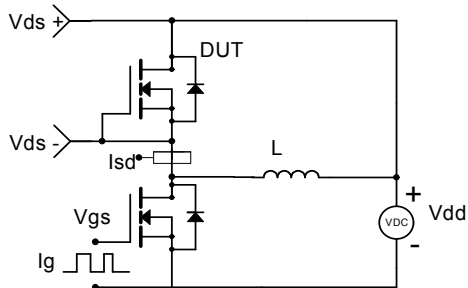
Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms



单击下面可查看定价，库存，交付和生命周期等信息

[>>AOS\(万代\)](#)